

### **Amendment to the Specification**

Please substitute the following amended paragraph for the paragraph beginning on p. 9, line 15:

According to another embodiment of the invention, the foregoing structure of the reflective color filter is altered, and the indium tin oxide layer 214 is not grown to obtain high-brightness reflective color filters. As illustrated in Fig. 4, a structure in Fig. 4 lacks the indium tin oxide layer 204, while the rest are the same as in Fig. 3. Table 2 lists process parameters of high-brightness reflective red and green color filters, including thicknesses of the silicon nitride layer 206, amorphous silicon layer 208, n-type silicon layer 210 and metal layer 212 and the radio frequency power of the chemical vapor deposition process for growing the silicon nitride layer 206. Moreover, the material of the metal layer 212 in Table 1 is chromium, and phosphorous is doped into the n-type silicon layer 210 therein.